

# QN7002

# N-CHANNEL MOSFET FOR SWITCHING

## Description

The QN7002, N-channel vertical type MOSFET designed for general-purpose switch, is a device which can be driven directly by a 4.5 V power source.

## Features

• Directly driven by a 4.5 V power source.

• Low on-state resistance

 $R_{DS(on)1} = 2.7 \ \Omega \ MAX. \ (V_{GS} = 10 \ V, \ I_D = 100 \ mA) \\ R_{DS(on)2} = 3.2 \ \Omega \ MAX. \ (V_{GS} = 4.5 \ V, \ I_D = 50 \ mA)$ 

## **Ordering Information**

Part Number	Lead Plating	Packing	Package
QN7002-T1B-AT	Pure Sn	3000p/Reel	SC-59 (Mini Mold)

**Remark** "-AT" indicates Pb-free. This product does not contain Pb in external electrode and other parts.

## **Remark for Agent**

ORDER NUMBER "2SK4079(1)" must be used to order, instead of "QN7002". For instance, "2SK4079(1)-T1B-AT"

## Absolute Maximum Ratings (T<sub>A</sub> = 25°C)

Drain to Source Voltage (V <sub>GS</sub> = 0 V)	VDSS	60	V
Gate to Source Voltage ( $V_{DS}$ = 0 V)	Vgss	±20	V
Drain Current (DC)	D(DC)	200	mA
Drain Current (pulse) <sup>Note</sup>	D(pulse)	±800	mA
Total Power Dissipation	Ρτ	200	mW
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

**Note** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

Caution This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

VESD ±400 V (MIL STD; C = 100 pF, R = 1.5 k $\Omega$ , 5 times), as reference value.

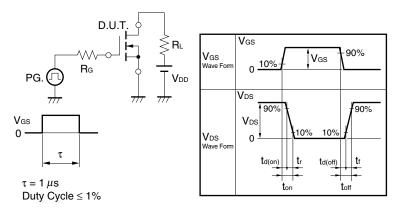


# Electrical Characteristics (T<sub>A</sub> = 25°C)

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μA
Gate Leakage Current	lgss	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±10	μA
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.0		2.5	V
Forward Transfer Admittance Note	y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 100 mA	150			mS
Drain to Source On-state Resistance <sup>Note</sup>	RDS(on)1	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 100 mA		2.1	2.7	Ω
	RDS(on)2	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 mA		2.4	3.2	Ω
Input Capacitance	Ciss	V <sub>DS</sub> = 10 V,		20		pF
Output Capacitance	Coss	V <sub>GS</sub> = 0 V,		9		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		2		pF
Turn-on Delay Time	td(on)	V <sub>DD</sub> = 10 V,		16		ns
Rise Time	tr	I⊳ = 200 mA,		6.5		ns
Turn-off Delay Time	td(off)	V <sub>GS</sub> = 10 V,		82		ns
Fall Time	tr	R <sub>G</sub> = 10 Ω		32		ns
Total Gate Charge	QG	I <sub>D</sub> = 200 mA, V <sub>DD</sub> = 25 V, V <sub>GS</sub> = 10 V		2		nC
Body Diode Forward Voltage	VF(S-D)	IF = 200 mA, VGS = 0 V		0.86		V

Note Pulsed

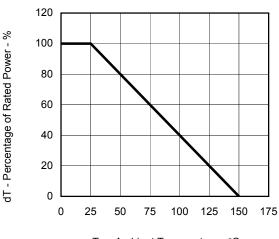
# **Test Circuit Switching Time**





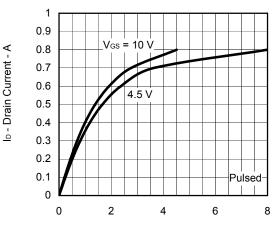
# Typical Characteristics (T<sub>A</sub> = 25°C)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

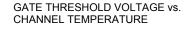


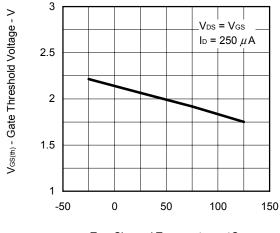
 $T_A-Ambient$  Temperature -  $^\circ C$ 





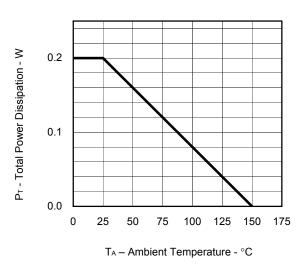
V<sub>DS</sub> - Drain to Source Voltage - V



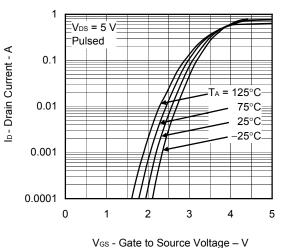


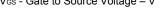
T<sub>ch</sub> - Channel Temperature - °C

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

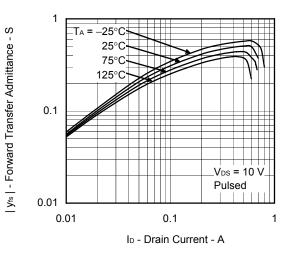


#### FORWARD TRANSFER CHARACTERISTICS

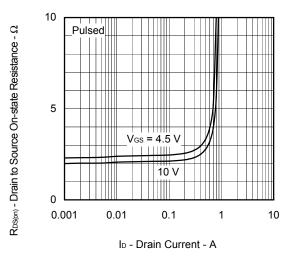




FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

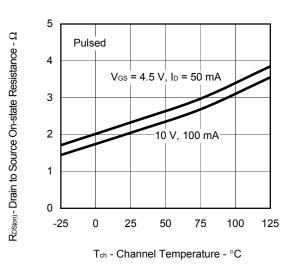




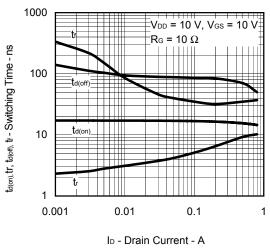


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

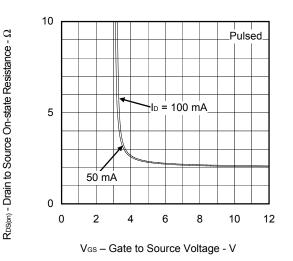
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



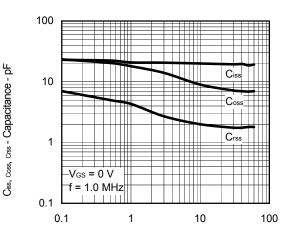


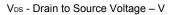


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

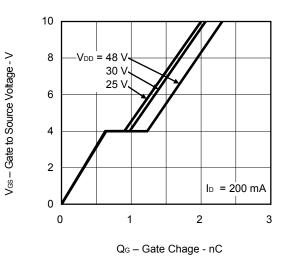


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



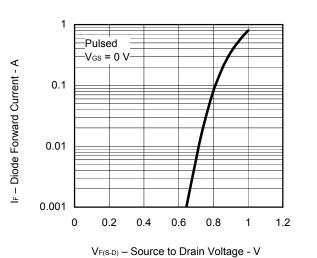


#### DYNAMIC INPUT CHARACTERISTICS



R07DS0269EJ0100 Rev.1.00

Mar 11, 2011

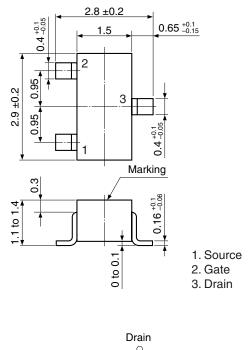


### SOURCE TO DRAIN DIODE FORWARD VOLTAGE

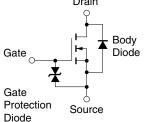


# Package Drawings (Unit: mm)

## SC-59 (Mini Mold)



# **Equivalent Circuit**



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.



<b>Revision History</b>	QN7002 Data Sheet
<b>Revision History</b>	QN700

		Description		
Rev.	Date	Page	Summary	
1.00	Mar 11, 2011	-	First Edition Issued	

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